TOSHIBA Transistor Silicon PNP · NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

RN4904FE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

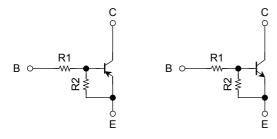
- Two devices are incorporated into an Extreme-Super-Mini (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.

 Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.

Equivalent Circuit and Bias Resistor Values

Q1

Q2

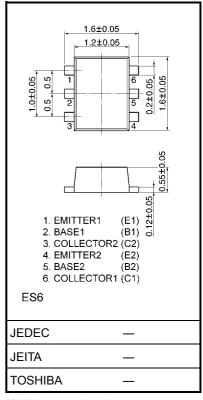


R1: 47 kΩ

R2: 47 kΩ

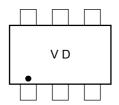
(Q1, Q2 common)

Unit: mm

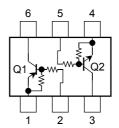


Weight: g (typ.)

Marking



Equivalent Circuit (top view)



Maximum Ratings (Ta = 25°C) (Q1)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-10	V
Collector current	Ic	-100	mA

Maximum Ratings (Ta = 25°C) (Q2)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	10	V
Collector current	I _C	100	mA

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P _C (Note)	100	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	−55~150	°C

Note: Total rating

2

Electrical Characteristics (Ta = 25°C) (Q1)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-100	nA
Collector cut-on current	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$	_	_	-500	ш
Emitter cut-off current	I _{EBO}	$V_{EB} = -10 \text{ V}, I_C = 0$	-0.082	_	-0.15	mA
DC current gain	h _{FE}	$V_{CE} = -5 \text{ V}, I_{C} = -10 \text{ mA}$	80	_	_	
Collector-emitter saturation voltage	V _{CE} (sat)	$I_C = -5 \text{ mA}, I_B = -0.25 \text{ mA}$	_	-0.1	-0.3	V
Input voltage (ON)	V _{I (ON)}	$V_{CE} = -0.2 \text{ V}, I_{C} = -5 \text{ mA}$	-1.5	_	-5.0	V
Input voltage (OFF)	V _{I (OFF)}	$V_{CE} = -5 \text{ V}, I_{C} = -0.1 \text{ mA}$	-1.0	_	-1.5	٧
Transition frequency	f _T	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	_	200	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	3	6	pF

Electrical Characteristics (Ta = 25°C) (Q2)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 50 \text{ V}, I_{E} = 0$	_	_	100	nA
	I _{CEO}	V _{CE} = 50 V, I _B = 0	_	_	500	шА
Emitter cut-off current	I _{EBO}	V _{EB} = 10 V, I _C = 0	0.082	_	0.15	mA
DC current gain	h _{FE}	V _{CE} = 5 V, I _C = 10 mA	80	_	_	
Collector-emitter saturation voltage	V _{CE} (sat)	$I_C = 5 \text{ mA}, I_B = 0.25 \text{ mA}$	_	0.1	0.3	V
Input voltage (ON)	V _{I (ON)}	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	1.5	_	5.0	V
Input voltage (OFF)	V _{I (OFF)}	$V_{CE} = 5 \text{ V}, I_{C} = 0.1 \text{ mA}$	1.0	_	1.5	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 5 mA	_	250	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	3	6	pF

Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input resistor	R1	_	32.9	47	61.1	kΩ
Resistor ratio	R1/R2		0.9	1.0	1.1	

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